MR45V256A

256k(32,768-Word × 8-Bit) FeRAM (Ferroelectric Random Access Memory) SPI

GENERAL DESCRIPTION

The MR45V256A is a nonvolatile 32,768-word x 8-bit ferroelectric random access memory (FeRAM) developed in the ferroelectric process and silicon-gate CMOS technology. The MR45V256A is accessed using Serial Peripheral Interface.Unlike SRAMs, this device, whose cells are nonvolatile, eliminates battery backup required to hold data. This device has no mechanisms of erasing and programming memory cells and blocks, such as those used for various EEPROMs. Therefore, the write cycle time can be equal to the read cycle time and the power consumption during a write can be reduced significantly.
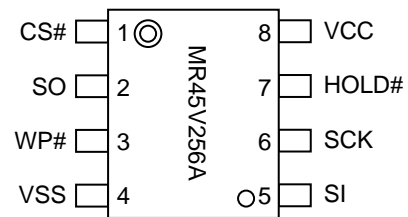The MR45V256A can be used in various applications, because the device is guaranteed for the write/read tolerance of 10^{12} cycles per bit and the rewrite count can be extended significantly.

FEATURES

- 32,768-word × 8-bit configuration (Serial Peripheral Interface : SPI)
- A single 3.3 V ± 0.3 V   power supply
- Operating frequency: 15MHz
- Read/write tolerance 10^{12} cycles/bit
- Data retention   10 years
- Guaranteed operating temperature range   −40 to 85°C (Extended temperature version)
- Package options:
   8-pin plastic SOP (P-SOP8-200-1.27-T2K   )

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PIN CONFIGURATION

8-pin plastic SOP

```
        CS# ⊐  1 ◎        8  ⊏ VCC
                   M
         SO ⊐  2  R        7  ⊏ HOLD#
                   4
                   5
        WP# ⊐  3  V        6  ⊏ SCK
                   2
                   5
                   6
         VSS ⊐  4  A     ○5  ⊏ SI
```

Note:
Signal names that end with # indicate that the signals are negative-true logic.

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PIN DESCRIPTIONS

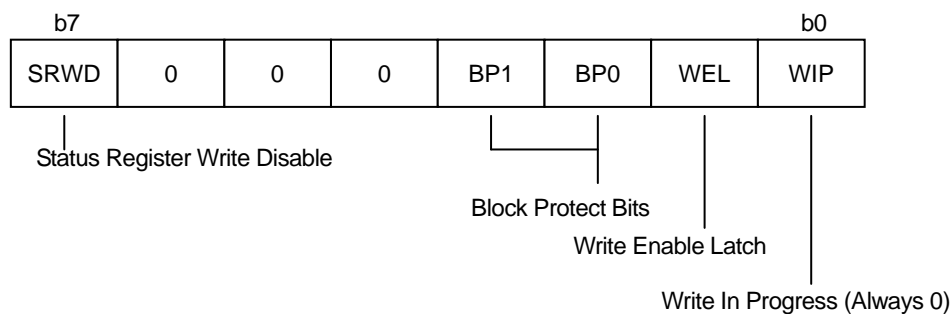| Pin Name	Description
CS#	Chip Select (input, negative logic) 　Latches an address by low input, activates the FeRAM, and enables a read or write operation.
WP#	Write Protect(input , negative logic) 　Write Protect pin controls write-operation to the status-register(BP0,BP1). This pin should be fixed low or high in write-operations.
HOLD#	HOLD(input , negative logic) 　Hold pin is used when the serial-communication suspended without disable the chip select. When HOLD# is low ,the serial-output is in High-Z status and serial-input/serial-clock are "Don't Care" . CS# should be low in hold operation.
SCK	Serial Clock 　Serial Clock is the clock input pin for setting for serial data timing. Inputs are latched on the rising edge and output occur on the falling edge.
SI	Serial input 　SI pins are serial input pins for Operation-code , addresses ,and data-inputs .
SO	Serial output 　SO pins are serial output pins.
V_{CC}, V_{SS}	Power supply 　Apply the specified voltage to V_{CC}. Connect V_{SS} to ground.

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SPI mode0（CPOL=0, CPHA=0）
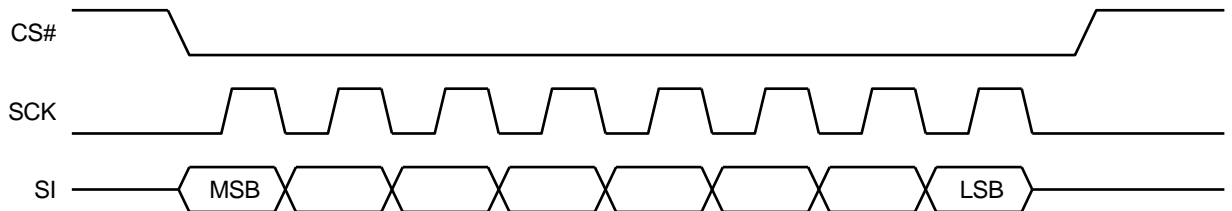
SPI mode3（CPOL=1, CPHA=1）
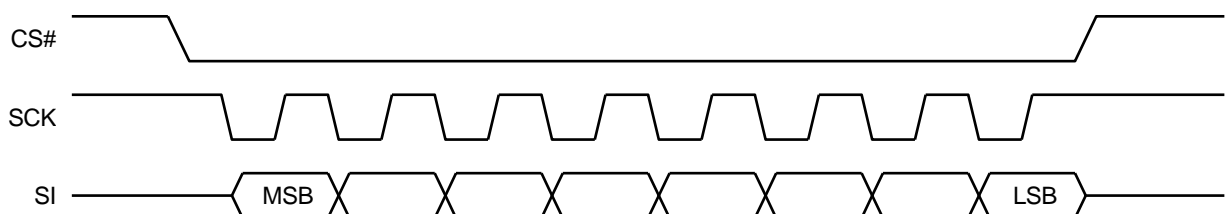
Status Register

Name	Function
WIP	Fixed to 0.
WEL	Write Enable Latch. This indicates internal WEL condition.
BP0,BP1	Block Protect :These bits can be changed protect area . This is the software protect.
SRWD	Status Register Write Disable（SRWD）: SRWD controls the effect of the hardware WP# pin. This device will be in hardware-protect by combination of SRWD and WP#.
0	Fixed to 0.

Status Register data are volatile.
Set Status Register data by WRSR(Write status register) command, after power on.

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Operation-Code

Operation codes are listed in the table below.If the device receives invalid operation code,the device will be diselected.

| Instruction	Description	Instruction format
WREN	Write Enable	0000 0110
WRDI	Write Disable	0000 0100
RDSR	Read Status Register	0000 0101
WRSR	Write Status Register	0000 0001
READ	Read from Memory Array	0000 0011
WRITE	Write to Memory Array	0000 0010

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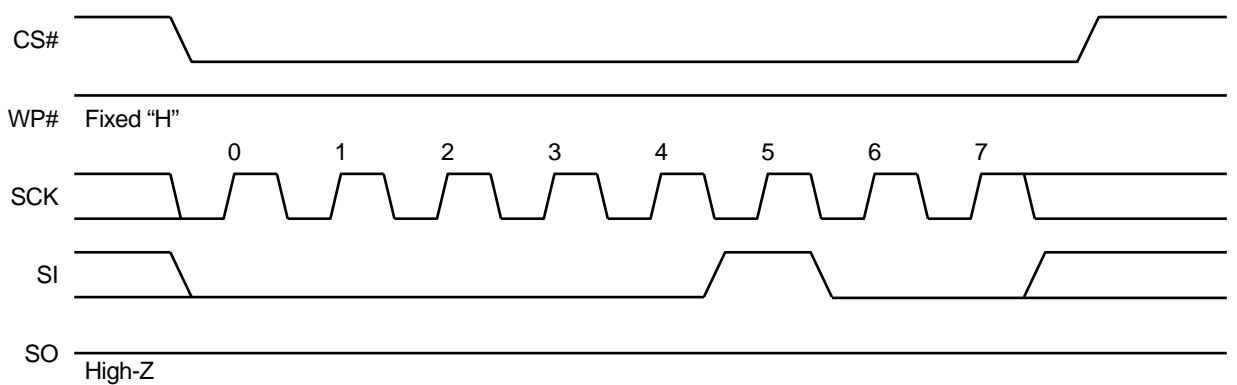**Commands**

WREN(Write Enable)

It is necessary to set Write Enable Latch（WEL）bit before write-operation (WRITE and WRSR).
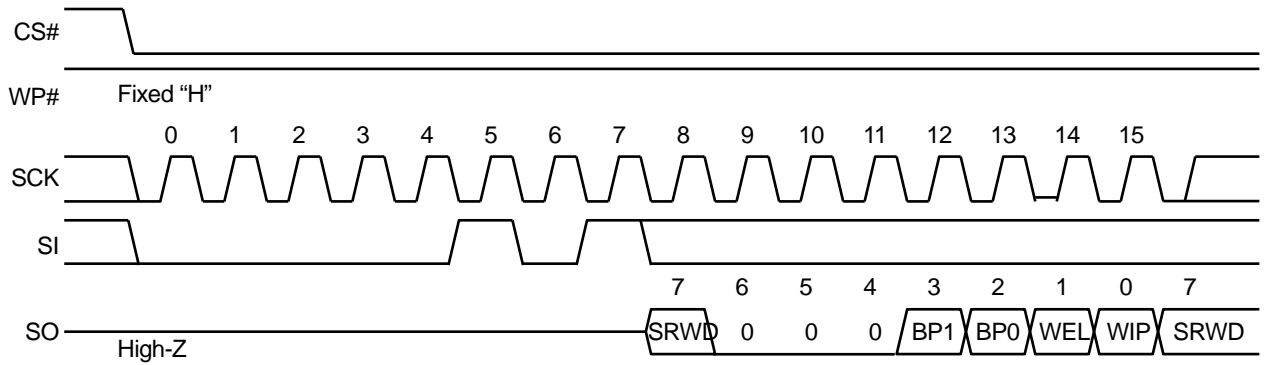
WREN command sets WEL bit.
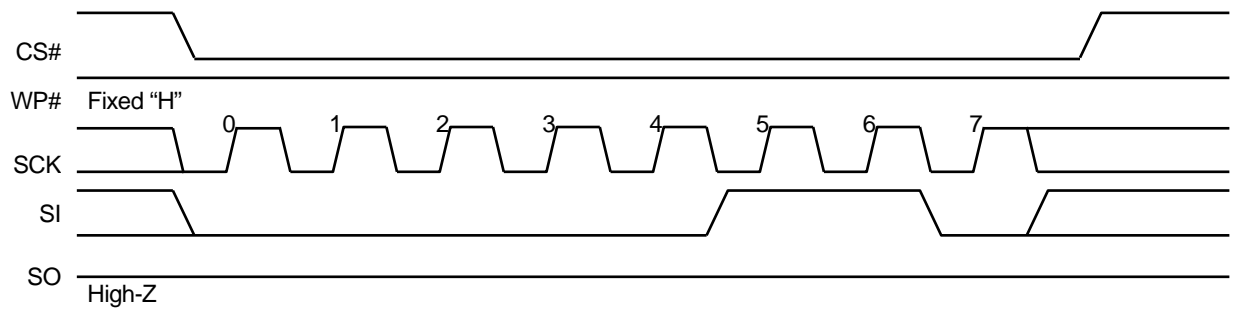
WRDI(Write Disable)

WRDI command resets WEL bit.

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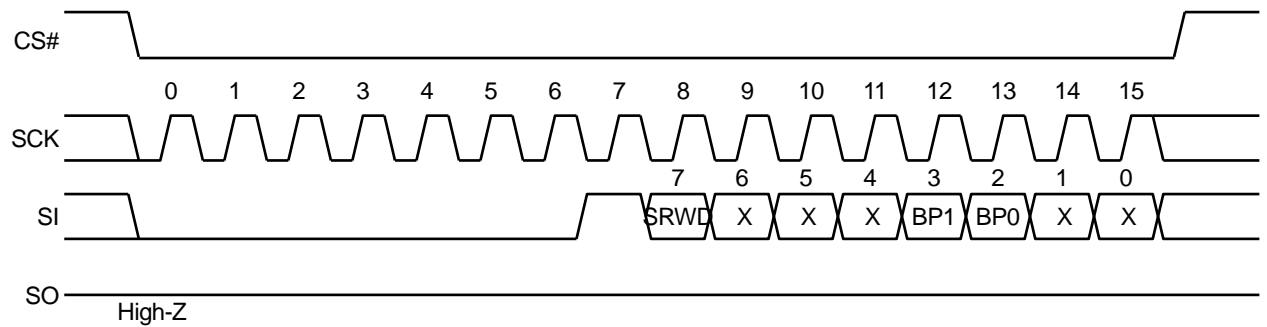
RDSR(READ Status Register)

The RDSR command allows to read data of status register.

WRSR(WRITE Status Register)

WRSR command allows to write data to status register(SRWD,BP0,BP1). It is necessary to set Write Enable
Latch（WEL）bit by WREN command before executing WRSR.

Note:
 WP#=Fix "H"

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READ(Read from Memory Array)

READ command can be valid when CS# goes "L",then the op-code and 16bit-adresses are inputted to serial input"SI".   The inputted adresses are loaded to internal register,then the data from corresponded address is output at serial-output "SO".If CS# will keep "L",the internal adress will be incresed automatically after 8 clocks and will output the data from new-address.When it reaches the most significant adress,the adress counter rolls over tostarting adress,and reading cycle can be continued infinitely.

Note : WP# = fixed "H"

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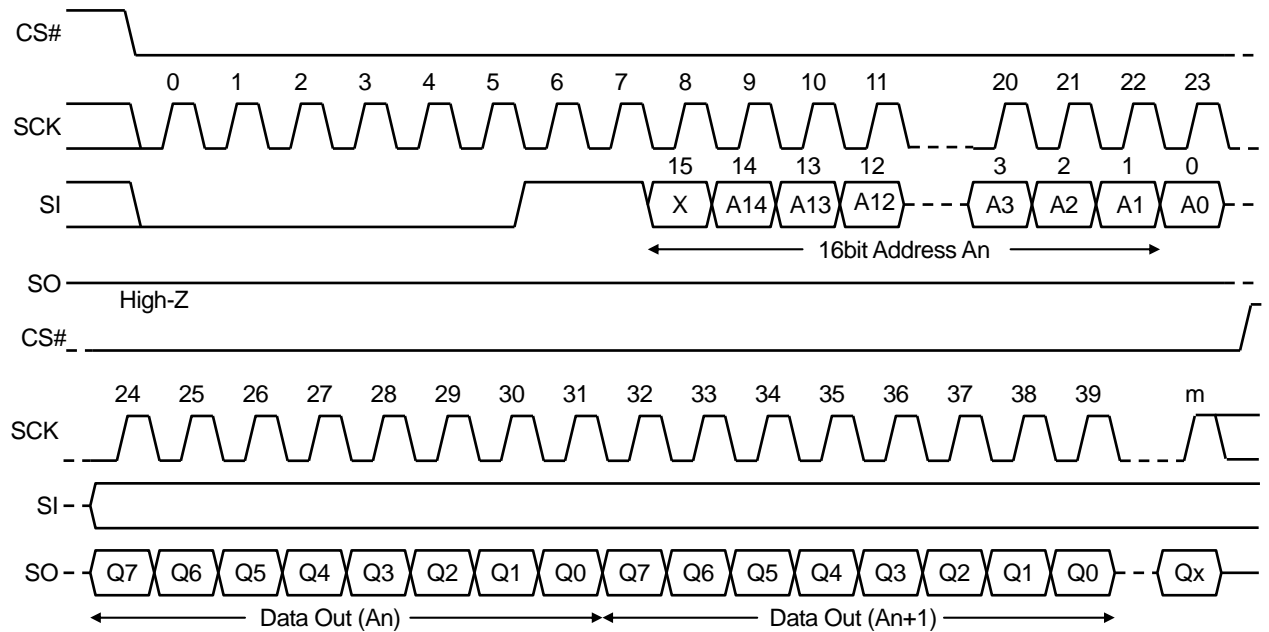
WRITE(Write to Memory Array）

Write command can be valid when CS# goes "L",then the op-code and 16bit-adresses are inputted to serial input"SI".   Writing is terminated when CS# goes high after data-input. If CS# will keep "L",the internal adress will be incresed automatically.When it reaches the most significant adress,the adress counter rolls over to starting adress 0000h,and writing cycle(overwriting) can be continued infinitely.
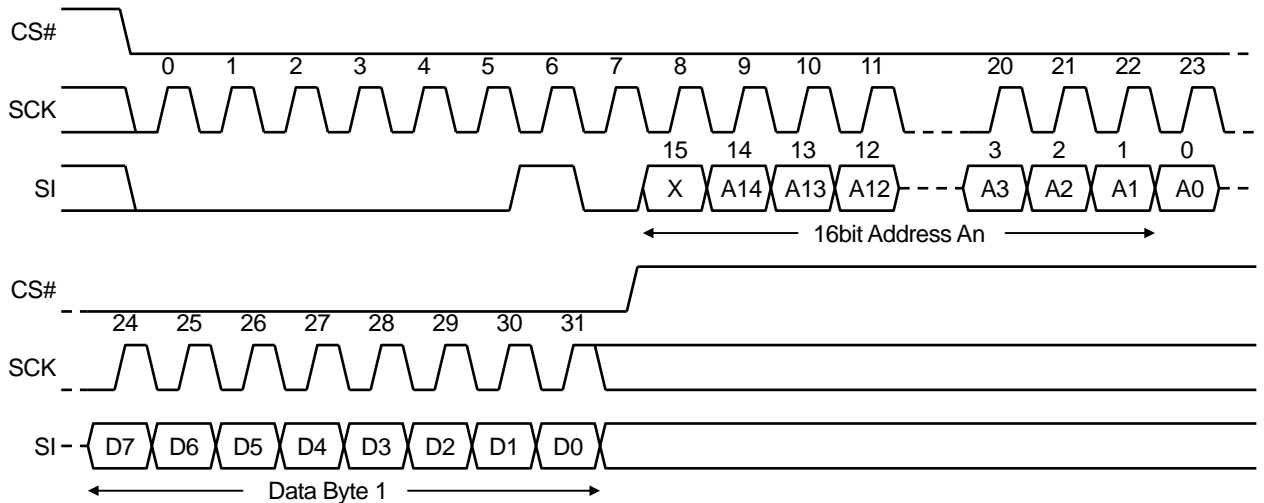
WRITE(1Byte)

Note : WP# = Fixed "H" , SO=High-Z

WRITE(Page)

Note : WP# = Fixed "H" , SO=High-Z

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Write Protection

Writing protection block is shown as follows:

Protect Block size

Block Protect BIT		Protected Block	Protected Address Area
BP1	BP0		
0	0	None	None
0	1	Upper 1/4 block	6000h – 7FFFh
1	0	Upper 1/2 block	4000h – 7FFFh
1	1	All	0000h – 7FFFh

Writing Protect

WP#	SRWD	mode	Writing protection status in status register	Protection status in memory	
				Protected blocks	Unprotected blocks
1	0	Software protection (SPM)	Status register is unprotected when WEL-bit is set by WREN command. BP0 and BP1 are unprotected.	Protected	Unprotected
0	0				
1	1				
0	1	Hardware protection (HPM)	Status register is protected. BP0 and BP1 are protected.	Protected	Unprotected

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HOLD

Hold status is used for suspending serial comunication without disable the chip. SO becomes "High-Z" and SI is "Don't care" during the hold status. It is necessary to keep CS#=L in hold status.

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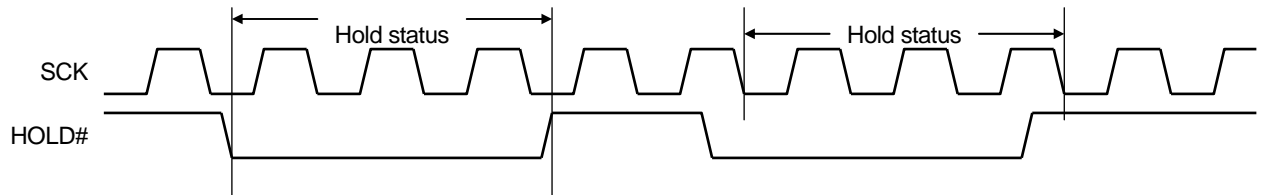
ELECTRICAL CHARACTERISTICS

Absolute Maximum Ratings
The application of stress (voltage, current, or temperature) that exceeds the absolute maximum rating may damage the device. Therefore, do not allow actual characteristics to exceed any one parameter ratings

Pin voltages

Parameter	Symbol	Rating		Unit
		Min.	Max.	
Pin Voltage (Input Signal)	V_{IN}	−0.5	$V_{CC} + 0.5$	V
Pin Voltage (Input/Output Voltage)	V_{INQ}, V_{OUTQ}	−0.5	$V_{CC} + 0.5$	V
Power Supply Voltage	V_{CC}	−0.5	4.0	V

Temperature Range

Parameter	Symbol	Rating		Unit	Note
		Min.	Max.		
Storage Temperature (Extended Temperature Version)	Tstg	−55	125	°C	
Operating Temperature (Extended Temperature Version)	Topr	−40	85	°C	

Others

Parameter	Symbol	Rating	Unit
Power Dissipation	P_D	1,000mW	
Allowable Input Current	I_{IN}	+/- 20mA	Ta=25°C
Allowable Output Current	I_{OUT}	+/- 20mA	Ta=25°C

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Recommended Operating Conditions

Power Supply Voltage

[V]

Parameter	Symbol	Min.	Typ.	Max.	Note
Power Supply Voltage	V_{CC}	3.0	3.3	3.6	
Ground Voltage	V_{SS}	0	0	0	

DC Input Voltage

[V]

Parameter	Symbol	Min.	Max.	Note
Input High Voltage	V_{IH}	V_{CC} x 0.8	$V_{CC}+0.3$	
Input Low Voltage	V_{IL}	−0.3	V_{CC} x 0.2	

Overshoot/Undershoot tolerance

Parameter	Symbol	Pulse Width	Peak
"H" input	$V_{IH\ OVERSHOOT}$	$\leq$ 20ns	$V_{CC}+1.0V$
"L" input	$V_{IL\ UNDERSHOOT}$	$\leq$ 20ns	− 1.0V

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DC Characteristics

DC Input/Output Characteristics

Parameter	Symbol	Condition	Min.	Max.	Unit	Note
Output High Voltage	V_{OH}	$I_{OH} = -2mA$	$V_{CC} \times 0.85$	—	V	
Output Low Voltage	V_{OL}	$I_{OL} = 2mA$	—	$V_{CC} \times 0.15$	V	
Input Leakage Current	I_{LI}	—	-10	10	µA	
Output Leakage Current	I_{LO}	—	-10	10	µA	

Power Supply Current

V_{CC}=Max.to Min, Ta=Topr

Parameter	Symbol	Condition	Max.	Unit	Note
Power Supply Current (Standby)	I_{CCS}	V_{IN}=0.2V or $V_{CC}-0.2V$	400	µA	
Power Supply Current (Operating)	I_{CCA}	V_{IN}=0.2V or $V_{CC}-0.2V$, SCK=15MHz, I_{OUT}=0mA	10	mA	

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AC Characteristics (Read Cycle)

V_{CC}=Max. to Min., Ta=Topr.

Parameter	Symbol	MR45V256A		Unit	Note
		Min.	Max.		
Clock frequency	f_C	D.C.	15	MHz	
CS# Active setup time	t_{SLCH}	10	—	ns	
CS# In-active setup-time	t_{SHCH}	10	—	ns	
CS# De-select time	t_{SHSL}	10	—	ns	
CS# Active hold time	t_{CHSH}	10	—	ns	
CS# In-active hold-time	t_{CHSL}	10	—	ns	
SCK High time	t_{CH}	30	—	ns	1
SCK Low time	t_{CL}	30	—	ns	1
SCK Rise time	t_{CLCH}	—	1	ns	2
SCK Fall time	t_{CHCL}	—	1	ns	2
Data Setup time	t_{DVCH}	5	—	ns	
Data Hold time	t_{CHDX}	5	—	ns	
SCK Low Hold time after HOLD# inactive	t_{HHCH}	10	—	ns	
SCK Low Hold time after HOLD# active	t_{HLCH}	10	—	ns	
SCK High Setup time before HOLD# active	t_{CHHL}	10	—	ns	
SCK High Setup time before HOLD# inactive	t_{CHHH}	10	—	ns	
Output disable time	t_{SHQZ}	—	20	ns	2
SCK Low to Output Valid time	t_{CLQV}	—	35	ns	
Output Hold time	t_{CLQX}	0	—	ns	
Output Rise time	t_{QLQH}	—	50	ns	2
Output Fall time	t_{QHQL}	—	50	ns	2
HOLD# High to Output Low impedance time	t_{HHQX}	—	20	ns	2
HOLD# High to Output High impedance time	t_{HLQZ}	—	20	ns	2

Note: 1. $t_{CH} + t_{CL} \geqq 1/f_C$
        2. sample value

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Timing Diagrams

Serial Input Timing

t_{SHSL}

CS#

t_{CHSL} t_{SLCH} t_{CHSH} t_{SHCH}

SCK

t_{DVCH} t_{CHDX} t_{CLCH} t_{CHCL}

SI MSB IN LSB IN

SO High Impedance

Hold Timing

CS#

t_{CHHL} t_{HLCH} t_{HHCH}

SCK

t_{CHHH}

t_{HLQZ} t_{HHQX}

SO

SI

HOLD#

Output Timing

CS#

t_{CH}

SCK

t_{CLQV} t_{CLQV} t_{CL}

t_{CLQX} t_{CLQX} t_{SHQZ}

SO LSB OUT

Address, LSB IN

t_{QLQH}
t_{QHQL}

SI

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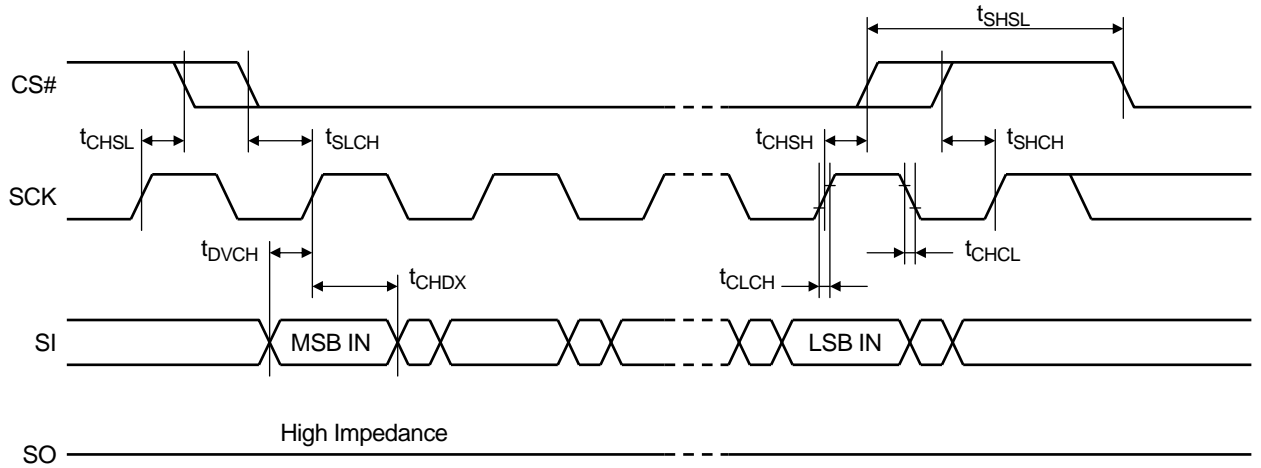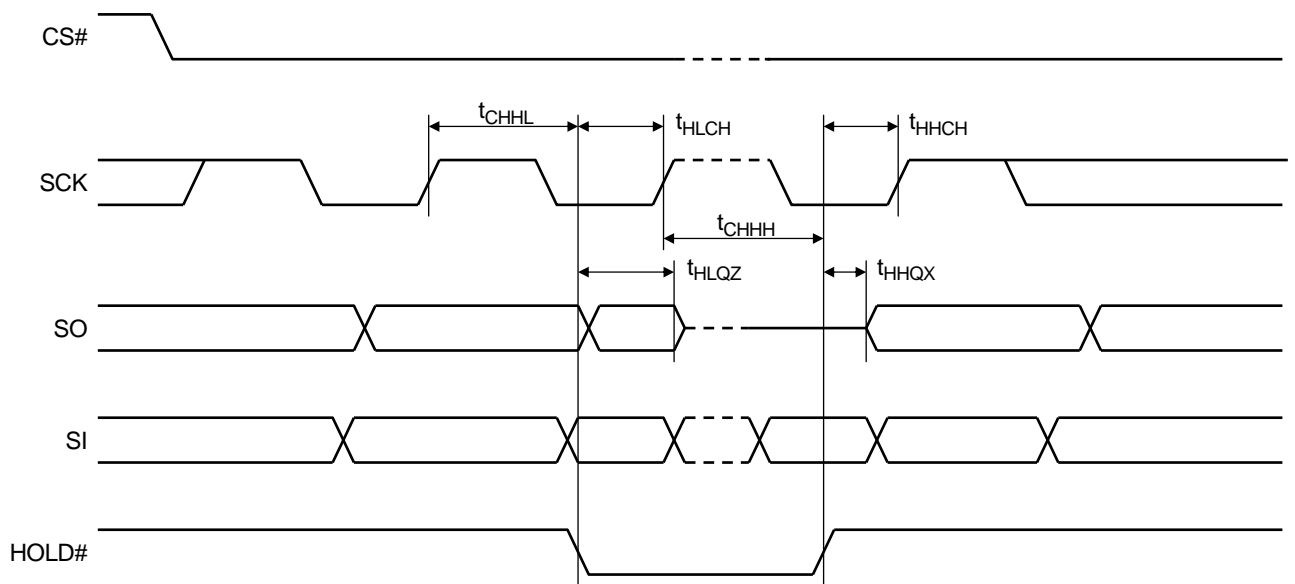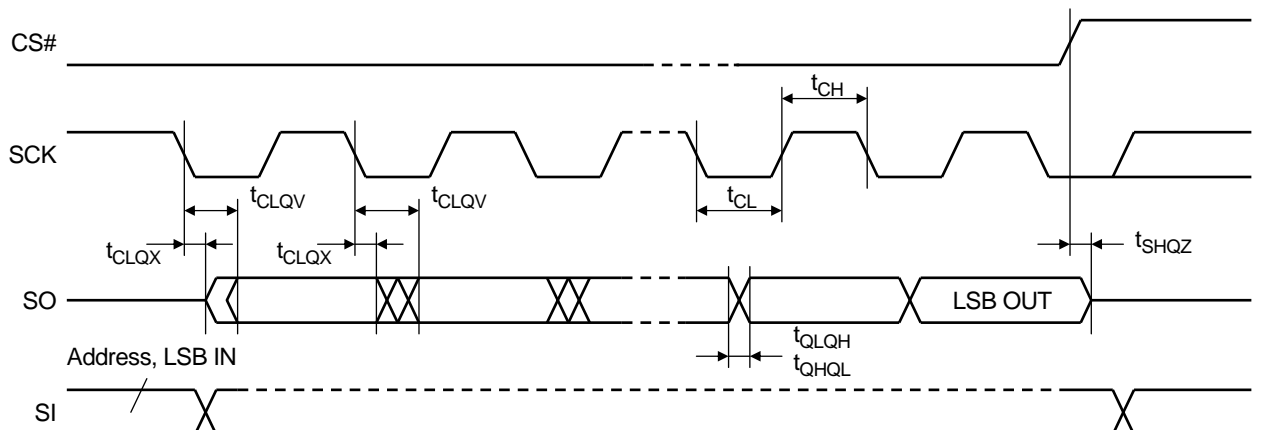
•Power-On and Power-Off Characteristics

(Under recommended operating conditions)

Parameter	Symbol	Min.	Max.	Unit	Note
Power-On CS# High Hold Time	t_{VHEL}	50	—	μs	1, 2
Power-Off CS# High Hold Time	t_{EHVL}	100	—	ns	1
Power-On Interval Time	t_{VLVH}	1	—	μs	2

Notes:

1. To prevent an erroneous operation, be sure to maintain CS#="H", and set the FeRAM in an inactive state (standby mode) before and after power-on and power-off.
2. Powering on at the intermediate voltage level will cause an erroneous operation; thus, be sure to power up from 0 V.
3. Enter all signals at the same time as power−on or enter all signals after power−on.

•Power-On and Power-Off Sequences

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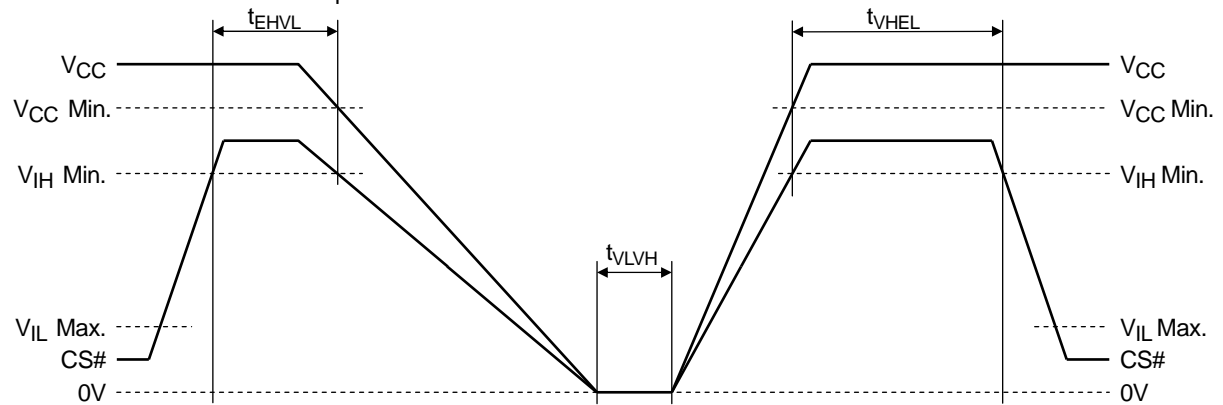
Read/Write Cycles and Data Retention

(Under recommended operating conditions)

Parameter	Min.	Max.	Unit	Note
Read/Write Cycle	10^{12}	—	Cycle	
Data Retention	10	—	Year	

Capacitance

Signal	Symbol	Min.	Max.	Unit	Note
Input Capacitance	C_{IN}	—	10	pF	1
Input/Output Capacitance	C_{OUT}	—	10	pF	1

Note:

Sampling value.   Measurement conditions are $V_{IN} = V_{OUT} = GND$, f = 1MHz, and Ta = 25°C

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REVISION HISTORY

Document No.	Date	Page Previous Edition	Page Current Edition	Description
PEDR45V256A-01	Jun. 03, 2010	–	–	Preliminary edition 1 from PJDR45V256A-03
PEDR45V256A-02	Sep. 10, 2010	1,13	1,13	Input Voltage
		7,8,9	7,8,9	fixed CS# waveform
		14	14	I_{CCS} I_{CCA}
PEDR45V256A-03	Mar. 04, 2011	1,12	1,12	temperature version $\Rightarrow$ Extended version
PEDR45V256A-04	Sep. 05, 2011	4 17	4 17	Status Register Input signal state in power-on
PEDR45V256A-05	Oct. 17, 2011	1-20	1-20	Changed corporate name and logo to LAPIS Semiconductor.

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